EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	104269	stress near9 (wafer or substrate or carrier or base or plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 08:46
L2	32902	stress near9 (wafer or substrate or carrier or base or plate) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base or plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 08:47
L3	7704	stress near9 (wafer or substrate or carrier or base or plate) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base or plate) and (cut$4 or dic$4 or singulat$4) near9 (wafer or substrate or carrier or base or plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 08:52
L4	3239	stress near9 (wafer or substrate or carrier or base or plate) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base or plate) and (cut$4 or dic$4 or singulat$4) near9 (wafer or substrate or carrier or base or plate) and (opening or via or hole or trench or aperture or groove or recess) near9 (insulat$4 or oxide or dielectric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 08:54

L5	2787	stress near9 (wafer or substrate or carrier or base or plate) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base or plate) and (cut$4 or dic$4 or singulat$4) near9 (wafer or substrate or carrier or base or plate) and (opening or via or hole or trench or aperture or groove or recess) near9 (insulat$4 or oxide or dielectric) and (circuit or die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 08:55
L6	132	stress near9 (wafer or substrate or carrier or base or plate) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base or plate) and (cut$4 or dic$4 or singulat$4) near9 (wafer or substrate or carrier or base or plate) and (opening or via or hole or trench or aperture or groove or recess) near9 (insulat$4 or oxide or dielectric) and (circuit or die) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 08:57
L7	8	stress near9 (wafer or substrate or carrier or base or plate) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base or plate) and (cut$4 or dic$4 or singulat$4) near9 (wafer or substrate or carrier or base or plate) and (opening or via or hole or trench or aperture or groove or recess) near9 (insulat$4 or oxide or dielectric) and (circuit or die) and pit and scribe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 09:01
L8	3628	(scribe near line) near9 (die or chip or circuit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 09:20

L9	1539	(scribe near line) near9 (die or chip or circuit) and (dielectric or oxide or insulat$4) near9 (wafer or semiconductor or carrier or base or plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 09:22
L10	1245	(scribe near line) near9 (die or chip or circuit) and (dielectric or oxide or insulat$4) near9 (wafer or semiconductor or carrier or base or plate) and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 10:06
L11	184	(scribe near line) near9 (die or chip or circuit) and (dielectric or oxide or insulat$4) near9 (wafer or semiconductor or carrier or base or plate) and metal and (scribe near line) near9 (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 10:18
L12	149	(scribe near line) near9 (die or chip or circuit) and (dielectric or oxide or insulat$4) near9 (wafer or semiconductor or carrier or base or plate) and metal and (scribe near line) near9 (dielectric or oxide or insulat$4) and (oxide or dielectric or insulat$4) near9 (opening or via or hole or trench or groove or recess or aperture)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/03 10:28
S1	861	(wafer or semiconductor or substrate) and dielectric and (open or via or hole or trench) and scribe and die and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S2	872	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02

S3	414	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S4	336	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:02
S5	272	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S6	206	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3 and region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:03
S7	27	(wafer or semiconductor or substrate) and dielectric and (opening or via or hole or trench) and scribe and die and (metal or conduct$4) and stress and plurality and expos$3 and region and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:19
S8	6	die and "scribe line" and (wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 08:24
S9	43	(wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit and "scribe line"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:02

S10	6	(wafer or semicondcutor or substrate) and dielectric and (opening or via or hole or trench) and (metal or conduct$4) and pit and "scribe line" and die	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 12:59
S11	194	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:05
S12	20	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and (scribe near4 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:06
S13	0	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and (scribe near4 line) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:13
S14	27	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:15

S15	15	((wafer or semiconductor or substrate) near4 die) and (dielectric or oxide or insulat$4) and (via or hole or trench or open$3) and (copper or tungsten) and (metal or polysilicon) and groove and photolithograph$8 and etch and pit and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:19
S16	33326	(stress near4 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S17	787	((stress near4 (wafer or semiconductor or substrate)) near4 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/10 14:17
S18	480	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:24
S19	70	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit$2 and (photolithographic$4 or etch$4) and plug and (metal or conduct$4 or polysilicon) and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/05/14 07:25

S20	63	(die near8 (wafer or semiconductor or substrate)) and (dielectric or oxide or insulat$4) and (open$3 or via or hole or trench or groove) and pit $2 and (photolithographic $4 or etch$4) and plug and (metal or conduct$4 or polysilicon) and (scribe near line) and (tungsten or copper)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:22
S21	21542	(die near9 (wafer or semiconductor or substrate)) and ((insulat $4 or oxide or dielectric) near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:23
S22	197081	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:24
S23	733	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:24
S24	30	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or (dielectric or oxide or insulat$4)) near9 (pit or recess))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 12:26

S25	12	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or (dielectric or oxide or insulat$4)) near9 (pit or recess)) and ((opening or via or hole or trench) near9 (dielectric or oxide or insulat$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:15
S26	3	((die or circuit) near9 (wafer or semiconductor or substrate)) and ((insulat$4 or oxide or dielectric) near9 (wafer or semiconductor or substrate)) and (scribe near9 die) and ((metal or (dielectric or oxide or insulat$4)) near9 (pit or recess)) and ((opening or via or hole or trench) near9 (dielectric or oxide or insulat$4)) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:23
S27	19949	stress near4 (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:24
S28	162	(stress near4 (dielectric or oxide or insulat$4)) near9 fill	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:25
S29	85	(stress near4 (dielectric or oxide or insulat$4)) near9 fill near9 (via or hole or trench or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:25
S30	12	(stress near4 (dielectric or oxide or insulat$4)) near9 fill near9 (via or hole or trench or opening) near9 (substrate or semiconductor or wafer)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/21 13:26

S31	58483	(stress near9 (wafer or semiconductor or substrate))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:38
S32	29190	(stress near9 (wafer or semiconductor or substrate or carrier)) and ((dielectric or oxide or insulat$4) near9 (wafer or semiconductor or substrate or carrier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:40
S33	33790	(High near stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:40
S34	451	(High near stress) near4 (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:41
S35	54	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:09
S36	0	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) and (scribe near4 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:42
S37	0	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) and (scribe near9 line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 11:42
S38	4	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:08

S39	3	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (substrate or wafer or carrier or semiconductor) near9 (recess or pit or aperture or hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:15
S40	19	(High near stress) near4 (dielectric or oxide or insulat$4) near9 (recess or pit or aperture or hole or via or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:32
S41	17	"high stress dielectric"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:33
S42	0	(pit or hole or recess or via or opening or aperture) near9 "high stress dielectric"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:34
S43	0	(pit or hole or recess or via or opening or aperture or trench) near9 "high stress dielectric"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:35
S44	5221	(high near k) near (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:36
S45	302	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:37
S46	302	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:37

S47	0	(high near k) near (dielectric or oxide or insulat$4) near9 pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:37
S48	9	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit) and (stress near9 relie $4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:38
S49	9	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit) and (stress near9 (relief or reliev$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 12:48
S50	18	(high near k) near (dielectric or oxide or insulat$4) near9 (via or hole or recess or aperture or trench or opening or pit) and (stress near9 (wafer or substrate or semiconductor carrier))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:01
S51	98	(high near stress) near (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:03
S52	2	(high near stress) near (dielectric or oxide or insulat$4) near9 (pit or trench or hole or aperture or recess or opening)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:04
S53	42	(stress near (relief or reliev$4)) and (semiconductor or substrate or wafer or carrier) near9 (dielectric or oxide or insulat$4) and die and (scribe near line) and (metal near9 (dielectric or oxide or film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:18

S54	24	(stress near (relief or reliev$4)) and (semiconductor or substrate or wafer or carrier) near9 (dielectric or oxide or insulat$4) and die and (scribe near line) and (metal near9 (dielectric or oxide or film)) and ((opening or hole or aperture or recess or via or trench) near9 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/19 13:19
S55	58547	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 07:43
S56	917	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal) and (stress near (relief or reliev$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 07:44
S57	0	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal) and (stress near (relief or reliev$4)) and die and (scribe near lin)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 07:44

S58	26	(wafer or semiconductor or substrate) near9 (dielectric or oxide or insulat$4) and (metal near9 (dielectric or oxide or insulat$4)) and ((opening or via or hole or trench or recess or aperture) near9 metal) and (stress near (relief or reliev$4)) and die and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 08:37
S59	5237	(high near k) near (dielectric or oxide or insulat$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 08:38
S60	302	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 08:41
S61	69	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench) near9 (substrate or wafer or semiconductor or carrier)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:02
S62	10	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench) near9 (substrate or wafer or semiconductor or carrier) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:06
S63	42	(high near k) near (dielectric or oxide or insulat$4) near9 (pit or recess or aperture or opening or via or hole or trench) and (substrate or wafer or semiconductor or carrier) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:10

S64	42	(pit or recess or aperture or opening or via or hole or trench) near9 ((high near k) near (dielectric or oxide or insulat$4)) and stress	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/24 09:11
S65	120	stress near9 (wafer or substrate or carrier or base) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base) and (via or trench or hole or opening or aperture or recess) near9 (dielectric or oxide or insulat$4) and (scribe near line) and die	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/31 12:11
S66	51	stress near9 (wafer or substrate or carrier or base) and (dielectric or oxide or insulat$4) near9 (wafer or substrate or carrier or base) and (via or trench or hole or opening or aperture or recess) near9 (dielectric or oxide or insulat$4) and (scribe near line) and die and pit$2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/31 12:12
S67	506409	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:35
S68	169542	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:36
S69	1799	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:42

S70	167	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit and (stress near9 (dielectric or oxide or insulat$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:45
S71	137	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit and (stress near9 (dielectric or oxide or insulat$4)) and circuit	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:46
S72	2	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit and (stress near9 (dielectric or oxide or insulat$4)) and circuit and die and (scribe near line)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:47
S73	2	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit and (stress near9 (dielectric or oxide or insulat$4)) and circuit and die and scribe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:48
S74	2	(dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit and (stress near9 (dielectric or oxide or insulat$4)) and die and scribe	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/02 15:48

| S75 | 3 | (dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) near9 (wafer or substrate or carrier or base or plate) and pit and (stress near9 (dielectric or oxide or insulat$4)) and scribe | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/02 15:48 |
| S76 | 4 | (dielectric or insulat$4 or oxide) near9 (opening or via or hole or trench or recess or aperture or groove) and pit and (stress near9 (dielectric or oxide or insulat$4)) and scribe | US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2008/03/02 15:52 |

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